

WHAT IS CLAIMED IS:

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1. A semiconductor device, comprising:
a first conductive layer;
a first ball formed on said first conductive layer;
a second conductive layer arranged spaced apart from said first
conductive layer;
a second ball formed on said second conductive layer; and
a bonding wire connecting said first and second balls; wherein
said second ball is formed by mechanically deforming said bonding
wire.
 2. The semiconductor device according to claim 1, wherein
said second ball is formed by bending said bonding wire on said
second conductive layer.
 3. The semiconductor device according to claim 1, wherein
said second ball is formed by making said bonding wire curved on
said second conductive layer.
 4. The semiconductor device according to claim 1, wherein
said first conductive layer includes an inner lead; and
said second conductive layer includes a bonding pad.
 5. The semiconductor device according to claim 1, comprising
a base;
a semiconductor element formed on said base with a die pad
interposed;
5 a sealing resin sealing said semiconductor element; and
an external terminal formed on a rear surface of said base; wherein
said first conductive layer includes a land formed on said base, and
said second conductive layer includes a bonding pad formed on said
semiconductor element.

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6. The semiconductor device according to claim 1, comprising:
a base;
first and second semiconductor elements mounted on said base with
a die pad interposed;
5 a sealing resin sealing said first and second semiconductor elements;
and
an external terminal formed on a rear surface of said base; wherein
said first conductive layer includes a first bonding pad formed on
said first semiconductor element, and
10 said second conductive layer includes a second bonding pad formed
on said second semiconductor element.

7. A method of manufacturing a semiconductor device, comprising:
a first bonding step of joining a first ball formed at a tip end of a
bonding wire to a first conductive layer;
after said first bonding step, joining said bonding wire to a second
5 conductive layer;
mechanically deforming said bonding wire on said second conductive
layer, with said bonding wire joined to the second conductive layer; and
a second bonding step of joining the deformed portion of said
bonding wire to said second conductive layer.

8. The method of manufacturing a semiconductor device according
to claim 7, wherein
said step of mechanically deforming said bonding wire includes the
step of bending said bonding wire on said second conductive layer.

9. The method of manufacturing a semiconductor device according
to claim 7, wherein
said step of mechanically deforming said bonding wire includes the
step of making said bonding wire curved on said second conductive layer.

